

## REQUEST FOR CONTINUED EXAMINATION

In accordance with 37 U.S.C. 1.114, a Request For Continued Examination (RCE) is filed concurrently with this Response To The Final Office Action so that the Office Action mailed October 26, 2000 (Paper No. 8) is effectively made non-final. Under 37 U.S.C. 1.114, the effect of the RCE, which makes the instant Office Action non-final, is to cause examination of the instant application to remain open. Accordingly, amendments and new claims submitted herein are to be entered as a matter of right, and *each* claim is entitled to continued examination, *particularly with respect to the responses provided herein.*

### AMENDMENTS

#### In the Claims

*Please cancel claims 11-13, without prejudice, waiver or disclaimer, and substitute the following clean copy text for the pending claims of the same number.*

- sub  
C'  
B
18. (ONCE AMENDED) A process comprising:
- providing a semiconductor substrate;
  - forming a gate oxide above the semiconductor substrate;
  - forming a first polycrystalline silicon layer over the gate oxide;
  - forming an interpoly dielectric;
  - forming a second polycrystalline silicon layer over the interpoly dielectric;
  - forming an anti-reflective coating above the second polycrystalline silicon layer;
  - patterning the device to form a stack; and
  - removing the antireflective coating without applying an oxide between the formation of the anti-reflective coating and the removal of the anti-reflective coating.

Please add the following new claims:

Sub C<sub>2</sub>

26. (New) A process comprising:  
providing a substrate;  
forming an anti-reflective coating above the substrate;  
patterning the substrate to form a stack; and  
removing the antireflective coating without applying an oxide between the formation of the anti-reflective coating and the removal of the anti-reflective coating.

B2

Sub D<sub>1</sub>

27. (New) The process of claim 27, wherein the anti-reflective coating comprises an oxide layer and a silicon oxynitride layer.

28. (New) The process of claim 27, wherein the silicon oxynitride is deposited by a plasma enhanced chemical vapor deposition process using the reactants  $N_2O$  and  $SiH_4$ .

29. (New) The process of claim 28, wherein the ratio of  $SiH_4$  to  $N_2O$  is maintained in the range of about 0.9-1.5:1.

30. (New) The process of claim 29, wherein the ratio of  $SiH_4$  to  $N_2O$  is maintained at about 1.22:1.

Sub E<sub>1</sub>

31. (New) The process of claim 26, wherein the removing of the antireflective coating comprises the step of etching with hot phosphoric acid.

Sub C<sub>3</sub>

32. (New) The process of claim 26, wherein the antireflective coating is removed before subjecting the anti-reflective coating to a temperature greater than about 400°C.